DMTH47M2LFVWQ-7 Datasheet

https://www.DiGi-Electronics.com

DiGi Electronics Part Number	DMTH47M2LFVWQ-7-DG
Manufacturer	Diodes Incorporated
Manufacturer Product Number	DMTH47M2LFVWQ-7
Description	MOSFET BVDSS: 31V~40V PowerDI333
Detailed Description	N-Channel 40 V 13.6A (Ta), 49A (Tc) 2.9W (Ta), 37.5 W (Tc) Surface Mount, Wettable Flank PowerDI3333 -8 (SWP) Type UX

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RFQ Email: Info@DiGi-Electronics.com

Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
DMTH47M2LFVWQ-7	Diodes Incorporated
Series:	Product Status:
-	Active
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
40 V	13.6A (Ta), 49A (Tc)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
4.5V, 10V	8.9mOhm @ 20A, 10V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
2.3V @ 250µA	12.3 nC @ 10 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±20V	881 pF @ 20 V
FET Feature:	Power Dissipation (Max):
-	2.9W (Ta), 37.5W (Tc)
Operating Temperature:	Grade:
-55°C ~ 175°C (TJ)	Automotive
Qualification:	Mounting Type:
AEC-Q101	Surface Mount, Wettable Flank
Supplier Device Package:	Package / Case:
PowerDI3333-8 (SWP) Type UX	8-PowerVDFN
Base Product Number:	
DMTH47	

Environmental & Export classification

RoHS Status:	REACH Status:
ROHS3 Compliant	REACH Unaffected
ECCN:	HTSUS:
EAR99	8541.29.0095

Lead-free Green

DMTH47M2LFVWQ

40V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET
PowerDI3333-8

Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D Max T_C = +25°C
40V	8.9mΩ @ V_{GS} = 10V	49.0A
	13.5mΩ @ V_{GS} = 4.5V	40.0A

Features and Benefits

- Rated to +175°C – Ideal for High Ambient Temperature Environments
- Low $R_{DS(ON)}$ – Ensures On-State Losses are Minimized
- Excellent Q_{gd} x $R_{DS(ON)}$ Product (FOM)
- Wettable Flank for Improved Optical Inspection
- 100% Unclamped Inductive Switching (UIS) Test in Production – Ensures More Reliable and Robust End Application
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The DMTH47M2LFVWQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**
  https://www.diodes.com/quality/product-definitions/

Description and Applications

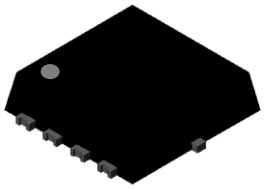
This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Backlighting
- Power-management functions
- DC-DC converters

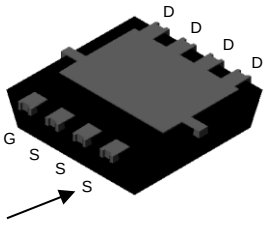
Mechanical Data

- Package: PowerDI®3333-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.027 grams (Approximate)

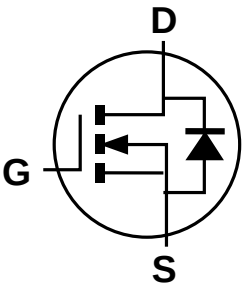
PowerDI3333-8 (SWP) (Type UX)



Top View



Bottom View



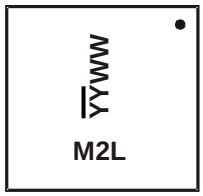
Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMTH47M2LFVWQ-7	PowerDI3333-8 (SWP) (Type UX)	2,000	Tape & Reel
DMTH47M2LFVWQ-13	PowerDI3333-8 (SWP) (Type UX)	3,000	Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

PowerDI3333-8 (SWP) (Type UX)



M2L = Product Type Marking Code
$\overline{YY}$WW = Date Code Marking
$\overline{YY}$ = Last Two Digits of Year (ex: 23 = 2023)
WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	40	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 5), V_{GS} = 10V		T_C = +25°C T_C = +100°C	I_D	49.0 34.7	A
Continuous Drain Current (Note 6), V_{GS} = 10V	Steady State	T_A = +25°C T_A = +100°C	I_D	13.6 9.6	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	196	A
Maximum Continuous Body Diode Forward Current (Note 5)			I_S	49	A
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)			I_{SM}	196	A
Avalanche Current, L = 0.1mH			I_{AS}	24	A
Avalanche Energy, L = 0.1mH			E_{AS}	28.8	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)	T_A = +25°C	P_D	2.9	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	52	°C/W
Total Power Dissipation (Note 5)	T_C = +25°C	P_D	37.5	W
Thermal Resistance, Junction to Case (Note 5)		$R_{\theta JC}$	4	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +175	°C

Notes: 5. Thermal resistance from junction to soldering point (on the exposed drain pad).
6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	40	—	—	V	V_{GS} = 0V, I_D = 250μA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	μA	V_{DS} = 32V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	1.2	—	2.3	V	V_{DS} = V_{GS}, I_D = 250μA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	6.6	8.9	mΩ	V_{GS} = 10V, I_D = 20A
		—	8.9	13.5		V_{GS} = 4.5V, I_D = 10A
Diode Forward Voltage	V_{SD}	—	0.87	1.2	V	V_{GS} = 0V, I_S = 20A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	881	—	pF	V_{DS} = 20V, V_{GS} = 0V f = 1MHz
Output Capacitance	C_{oss}	—	496	—		
Reverse Transfer Capacitance	C_{rss}	—	19.5	—		
Gate Resistance	R_g	—	2.06	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = 10V)	Q_g	—	12.3	—	nC	V_{DS} = 20V, I_D = 20A
Total Gate Charge (V_{GS} = 4.5V)	Q_g	—	5.8	—		
Gate-Source Charge	Q_{gs}	—	2.6	—		
Gate-Drain Charge	Q_{gd}	—	1.6	—		
Turn-On Delay Time	$t_{D(ON)}$	—	3.82	—	ns	V_{DD} = 20V, V_{GS} = 10V R_g = 3Ω, I_D = 20A
Turn-On Rise Time	t_R	—	4.76	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	12.6	—		
Turn-Off Fall Time	t_F	—	4.83	—		
Body Diode Reverse Recovery Time	t_{RR}	—	31.9	—	ns	I_F = 20A, dI/dt = 100A/μs
Body Diode Reverse Recovery Charge	Q_{RR}	—	25.0	—	nC	

Notes: 7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.

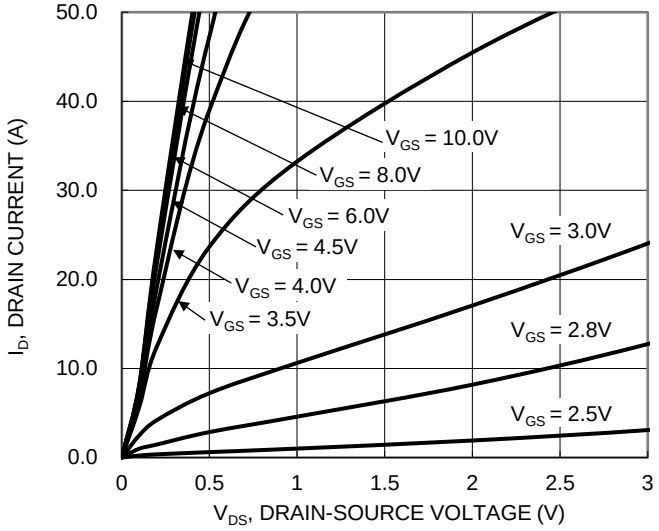


Figure 1. Typical Output Characteristic

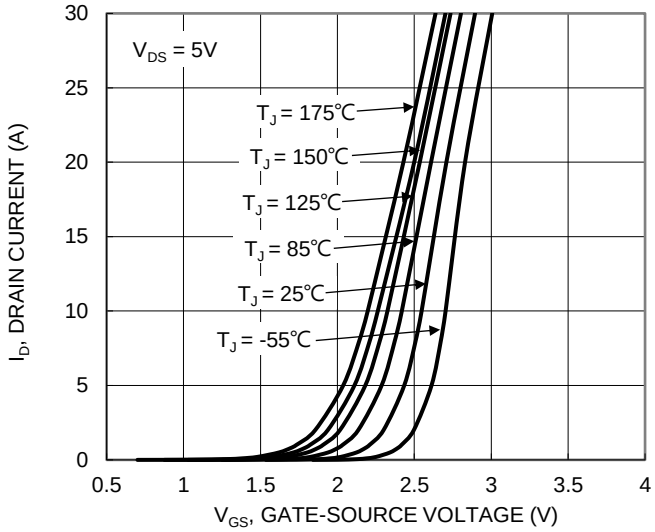


Figure 2. Typical Transfer Characteristic

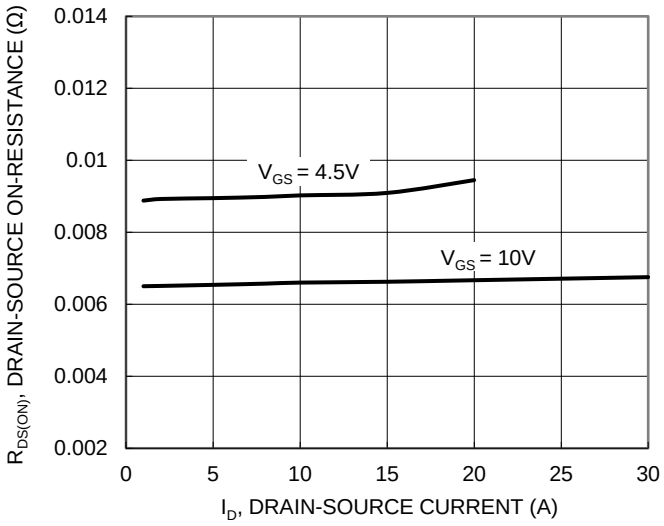


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

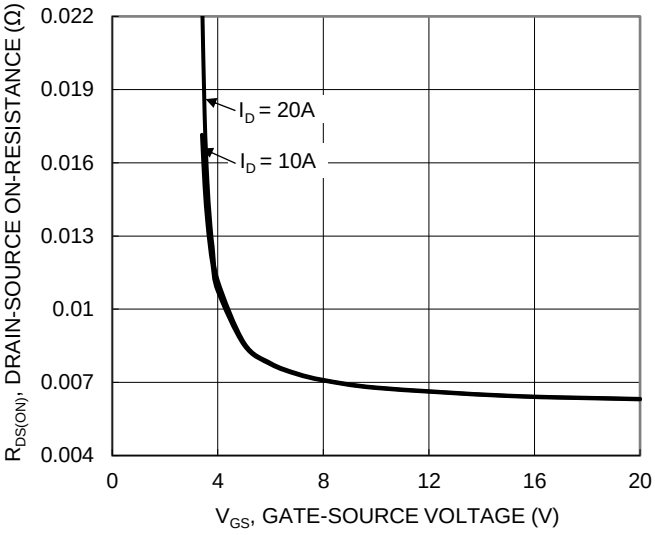


Figure 4. Typical Transfer Characteristic

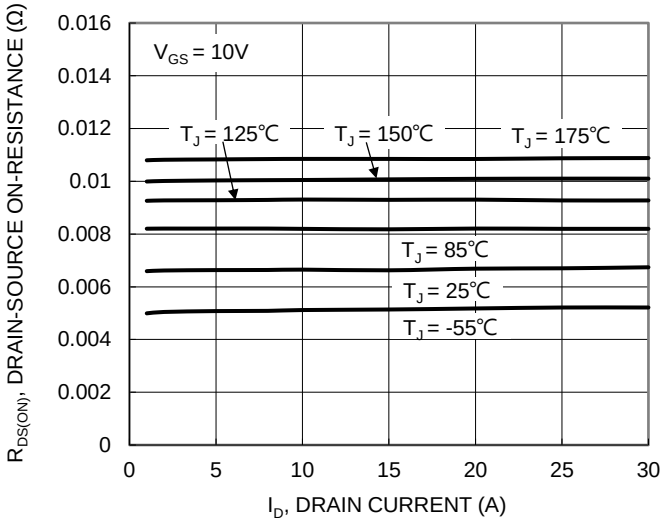


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

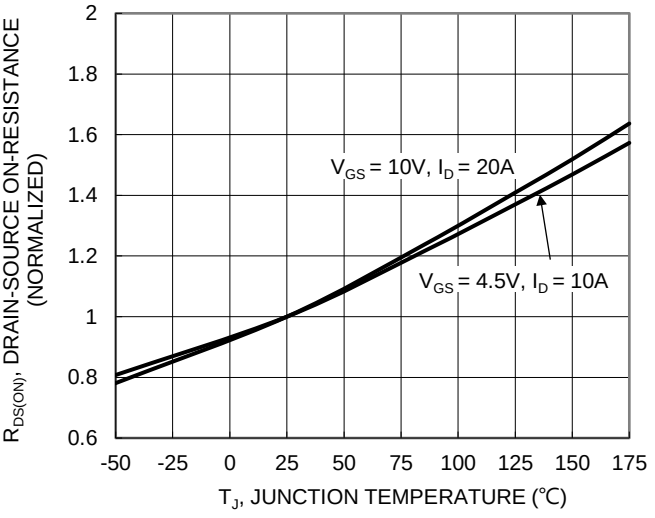


Figure 6. On-Resistance Variation with Junction Temperature

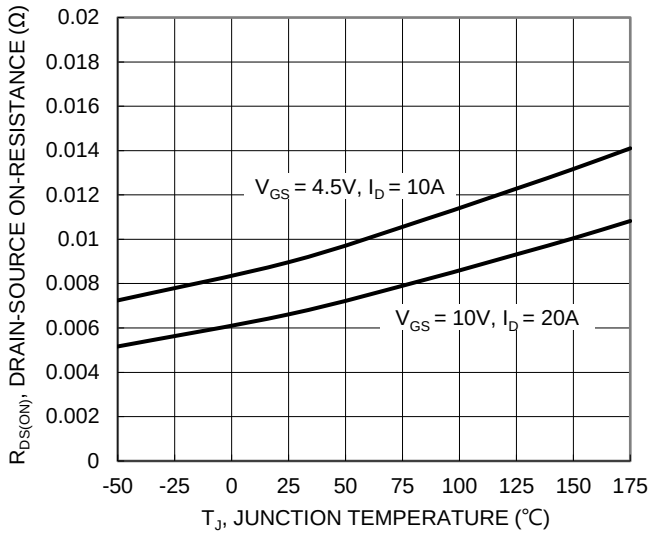


Figure 7. On-Resistance Variation with Junction Temperature

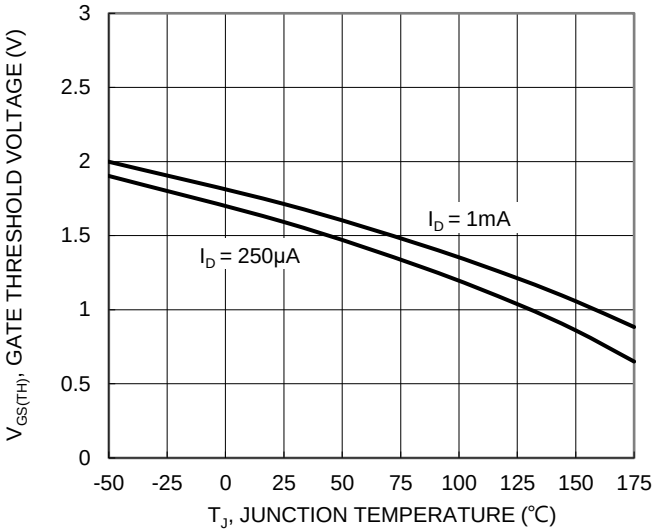


Figure 8. Gate Threshold Variation vs. Junction Temperature

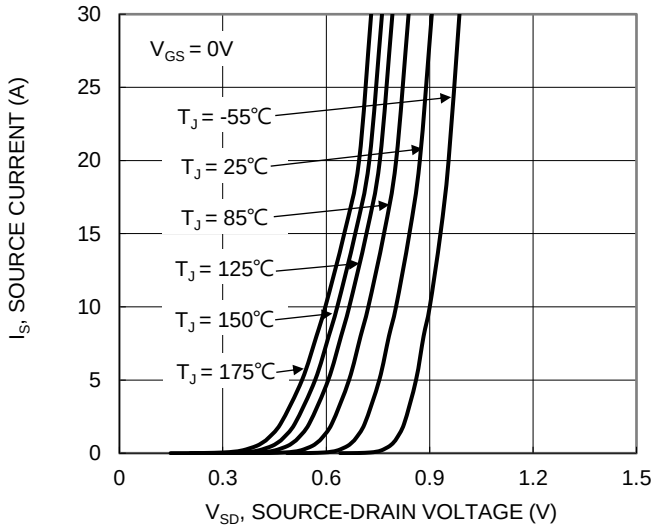


Figure 9. Diode Forward Voltage vs. Current

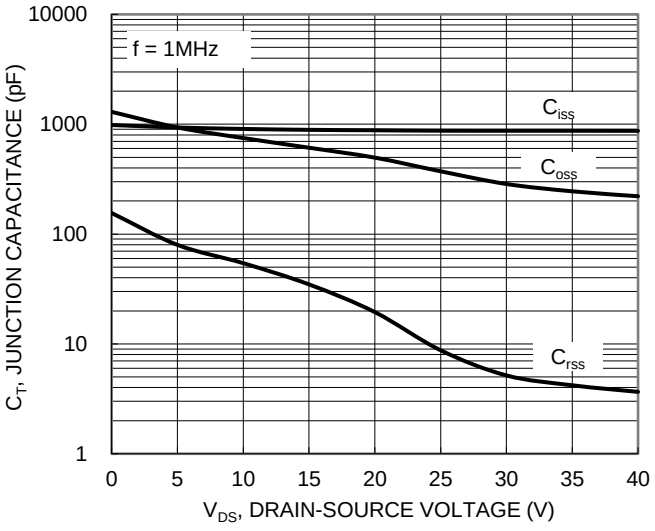


Figure 10. Typical Junction Capacitance

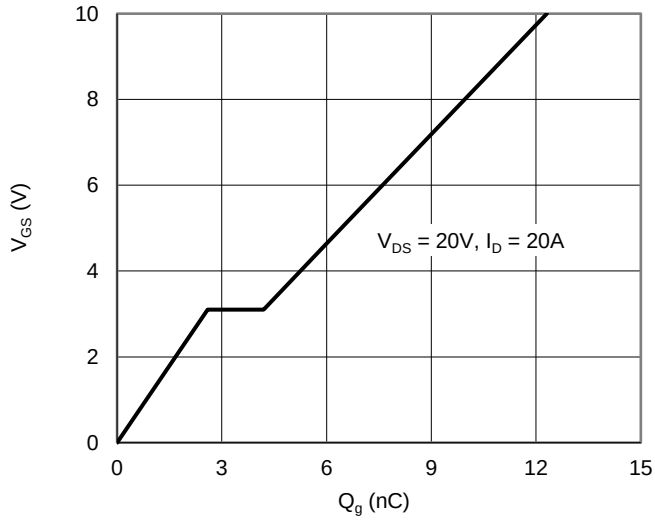


Figure 11. Gate Charge

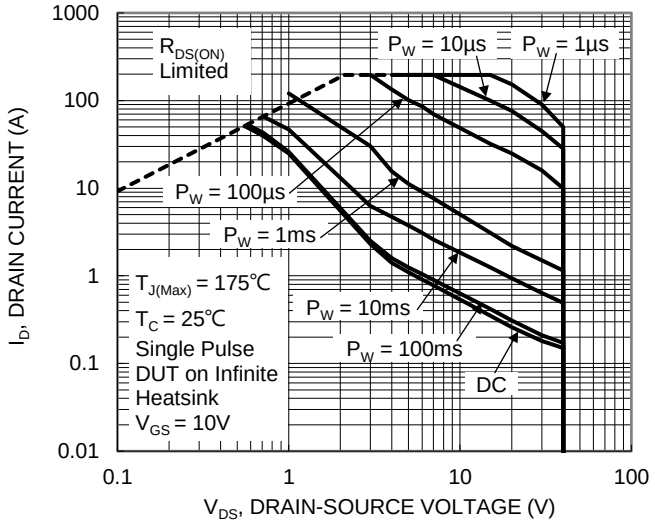


Figure 12. SOA, Safe Operation Area

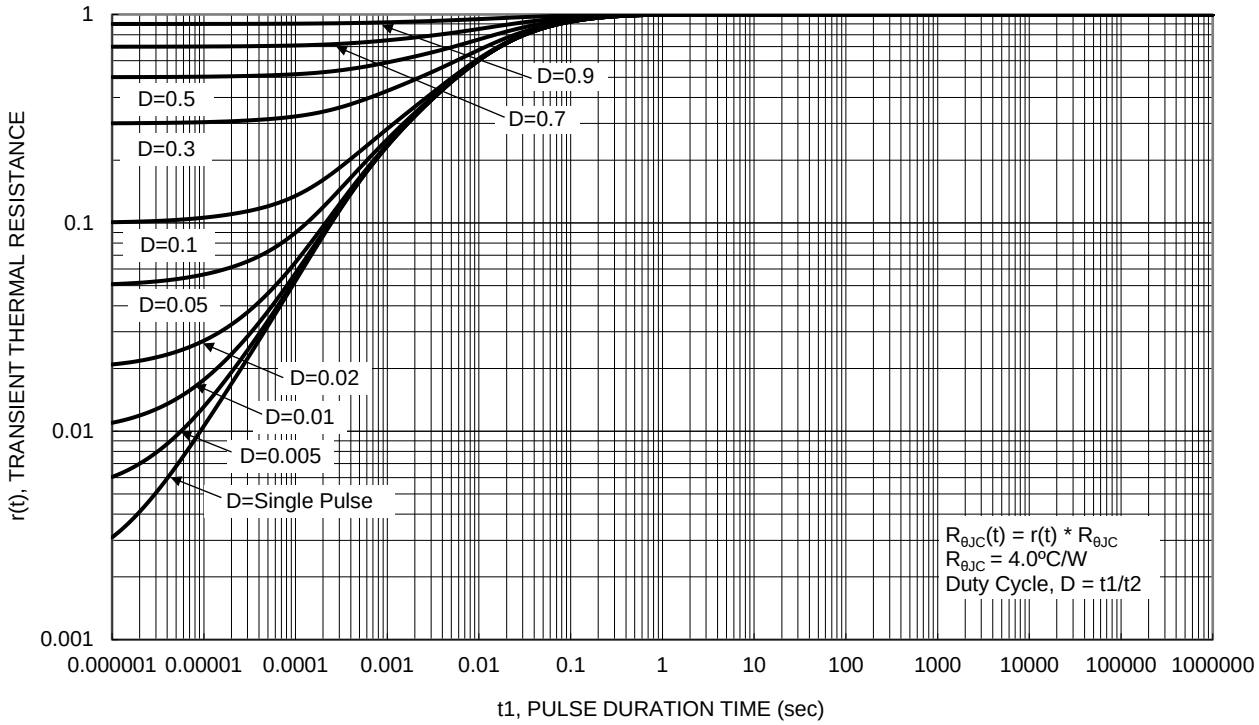
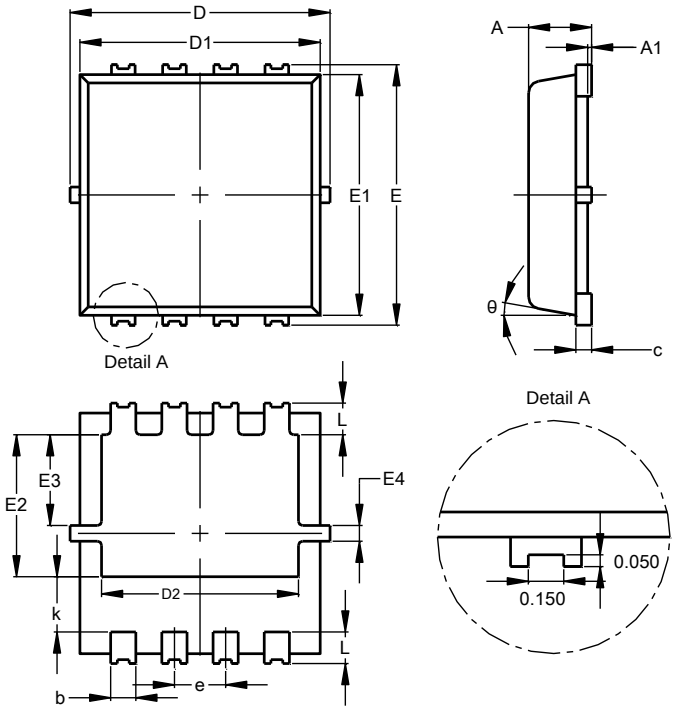


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)

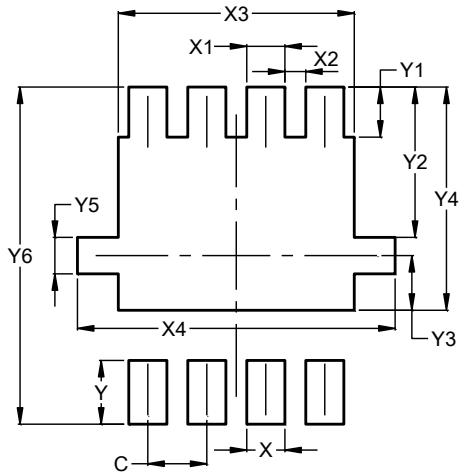


PowerDI3333-8 (SWP) (Type UX)			
Dim	**Min**	**Max**	**Typ**
A	0.75	0.85	0.80
A1	0.00	0.05	--
b	0.25	0.40	0.32
c	0.10	0.25	0.15
D	3.20	3.40	3.30
D1	2.95	3.15	3.05
D2	2.30	2.70	2.50
E	3.20	3.40	3.30
E1	2.95	3.15	3.05
E2	1.60	2.00	1.80
E3	0.95	1.35	1.15
E4	0.10	0.30	0.20
e	–	–	0.65
k	0.50	0.90	0.70
L	0.30	0.50	0.40
θ	0°	12°	10°
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.600
X4	3.500
Y	0.700
Y1	0.550
Y2	1.650
Y3	0.600
Y4	2.450
Y5	0.400
Y6	3.700

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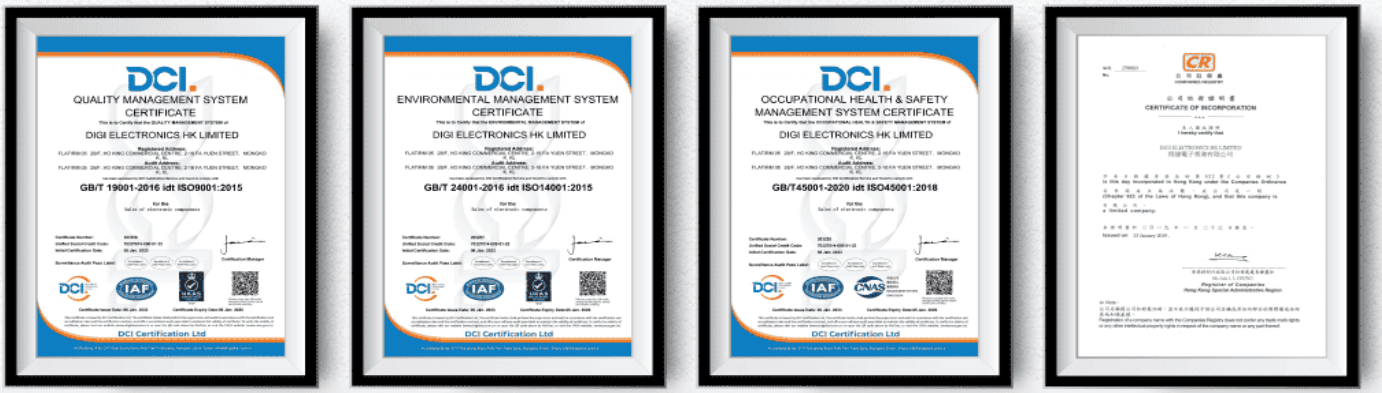

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